

In the Specification:

Please amend paragraph 17 as follows:

[0017] Experiments were conducted to test variations in the composition of a polishing fluid for second step polishing by CMP to remove a barrier film of TaN from an underlying dielectric layer of silica on a semiconductor wafer. Further, the same Experiments were conducted to remove copper metal from a semiconductor wafer, wherein, the copper metal simulated metal in trenches in a semiconductor wafer. With reference to Table 1, experiments were performed by polishing a barrier film of TaN and a dielectric layer of silica, using a polishing pad and a polishing fluid of basic pH, (pH=9). The pH=9 is a nominal value, as all concentrations of constituents in the polishing fluid are nominal values. Accordingly, all stated measurements of the constituents, as well as the pH measurement, are variable, respectively, about their stated nominal values. Also with reference to Table 1, Tests A and B use polishing fluids ~~containing~~ containing 0% abrasive and 0% citric acid as reference experiments, wherein 0.002 weight% or 0.1 wt% BTA was added respectively; Test C uses a polishing fluid containing 1% submicron silicon dioxide abrasive and 0% citric acid as a comparative experiment for testing performances of citric acid; the slurries of Tests 1 through 4 contain 1% silicon dioxide abrasive and increasing concentration of citric acid from 0.5% to 4%. —The polishing fluids listed in Table 1 may also comprise a small amount of a biocide. Using these polishing fluids, CMP was conducted on a polishing pad, IC1010 from Rodel Inc, polishing sheet blank wafers. For each polishing fluid, two TaN wafers, two copper wafers and two TEOS wafers were used. The reported removal rates in the table are an average of two wafers.